

AMENDMENT TO THE CLAIMS

The following claim listing replaces all prior listings and versions of the claims:

LISTING OF CLAIMS

1-27. (Cancelled)

28. (Currently amended) A field effect transistor comprising: a semiconductor layer through which carriers injected from a source region travel toward a drain region, the semiconductor layer being formed from a composite material comprising an organic semiconductor material and nanotubes, wherein

plural ones of the nanotubes are chemically joined with each other in the semiconductor layer.

29. (Currently amended) The field effect transistor according to claim 28, wherein the plural ones of the nanotubes are chemically joined by a connecting material and a joint portion between the joined nanotubes including the connecting material is coated with the organic semiconductor material in the semiconductor layer.

30-45. (Cancelled)

46. (Previously presented) The field effect transistor according to claim 28, wherein the nanotubes are carbon nanotubes.

47. (Previously presented) The field effect transistor according to claim 28, wherein the organic semiconductor material is a polymer-type organic semiconductor material.

48. (Previously presented) The field effect transistor according to claim 47, wherein the polymer-type organic semiconductor material is a thiophene-type material.

49. (Previously presented) The field effect transistor according to claim 28, wherein the organic semiconductor material is a low-molecular-weight organic semiconductor material.

50. (Previously presented) The field effect transistor according to claim 49, wherein the low-molecular-weight organic semiconductor material is an acene-type material.

51. (Previously presented) The field effect transistor according to claim 28, which is formed on a substrate.

52. (Previously presented) The field effect transistor according to claim 51, wherein the substrate is a plastic sheet or a resin film.

53. (Withdrawn) An active-matrix display comprising a plurality of field effect transistors as recited in claim 28 which are disposed as switching devices for driving pixels.

54. (Withdrawn) A wireless ID tag comprising a field effect transistor as recited in claim 28 which is used as a semiconductor device for forming an integrated circuit.

55. (Withdrawn) Portable equipment comprising a field effect transistor as recited in claim 28 which is used as a semiconductor device for forming an integrated circuit.

56. (New) The field effect transistor according to claim 28, wherein the plural ones of the nanotubes are chemically joined at an end of each nanotube.